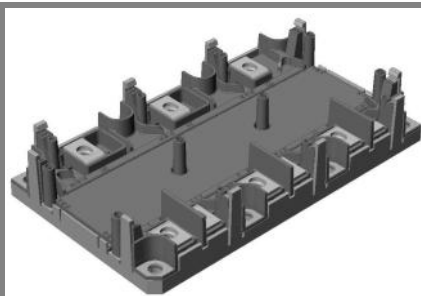


SKiM455GD12T4D1



SKiM[®] 5

Trench IGBT modules

SKiM455GD12T4D1

Preliminary Data

Features

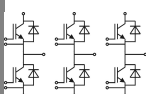
- IGBT 4 = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications*

- High Reliability AC inverter drives
- UPS

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max
- $T_{j,max}$ of the diode is limited to 150°C

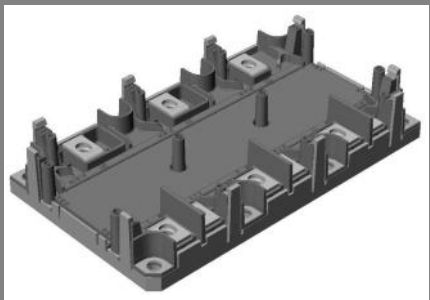


GD

Absolute Maximum Ratings			T _c = 25 °C, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = °C		1200	V
I _C	T _j = 150 °C	T _{heatsink} = 25 °C	400	A
		T _{heatsink} = 70 °C	305	A
I _{CRM}	I _{CRM} = 3xI _{CNOM}		1350	A
V _{GES}			± 20	V
t _{psc}	V _{CC} = 800 V; V _{GE} ≤ 15 V; T _j = 150 °C V _{CES} < 1200 V		10	µs
Inverse Diode				
I _F	T _j = 150 °C	T _{heatsink} = 25 °C	295	A
		T _{heatsink} = 70 °C	215	A
I _{FRM}	I _{FRM} = 2 x I _{FNOM}		600	A
Module				
I _{t(RMS)}				A
T _{vj}			-40 ... +150	°C
T _{stg}			-40 ... +125	°C
V _{isol}	AC, 1 min.		2500	V

Characteristics			T _c = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 18 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C				0,3	mA
V _{CE0}	T _j = 25 °C			0,8	0,9	V
	T _j = 125 °C			0,7	0,8	V
r _{CE}	V _{GE} = 15 V T _j = 25°C			2,2	2,4	mΩ
	T _j = 125°C			3,1	3,3	mΩ
V _{CE(sat)}	I _{Cnom} = 450 A, V _{GE} = 15 V T _j = 25°C _{chiplev.}			1,8	2	V
	T _j = 125°C _{chiplev.}			2,1	2,3	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			27,9		nF
C _{oes}				1,7		nF
C _{res}				1,5		nF
Q _G	V _{GE} = -8V/+15V			2600		nC
R _{Gint}	T _j = 25 °C			1,7		Ω
t _{d(on)}	R _{Gon} = 1 Ω V _{CC} = 600V di/dt = 8200 A/μs I _C = 450A			265		ns
t _r				60		ns
E _{on}				34		mJ
t _{d(off)}	R _{Goff} = 1 Ω T _j = 125 °C di/dt = 5300 A/μs V _{GE} = ± 15V			470		ns
t _f				65		ns
E _{off}				40		mJ
R _{th(j-s)}	per IGBT			0,14		K/W

SKiM455GD12T4D1



SKiM[®] 5

Trench IGBT modules

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Preliminary Data

Features

- IGBT 4 = Trenchgate technology
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- High short circuit capability

Typical Applications*

- High Reliability AC inverter drives
- UPS

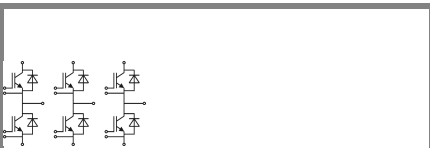
Remarks

- Case temperature limited to $T_c = 125^{\circ}\text{C}$ max
- $T_{j,max}$ of the diode is limited to 150°C

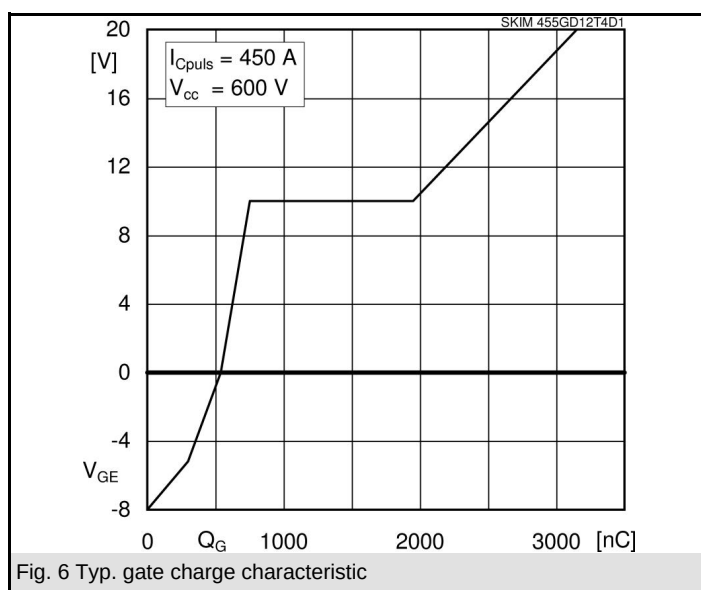
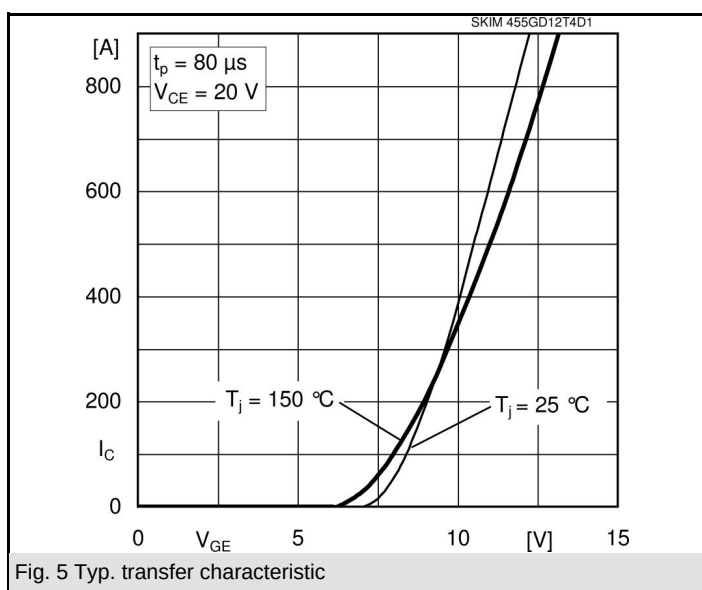
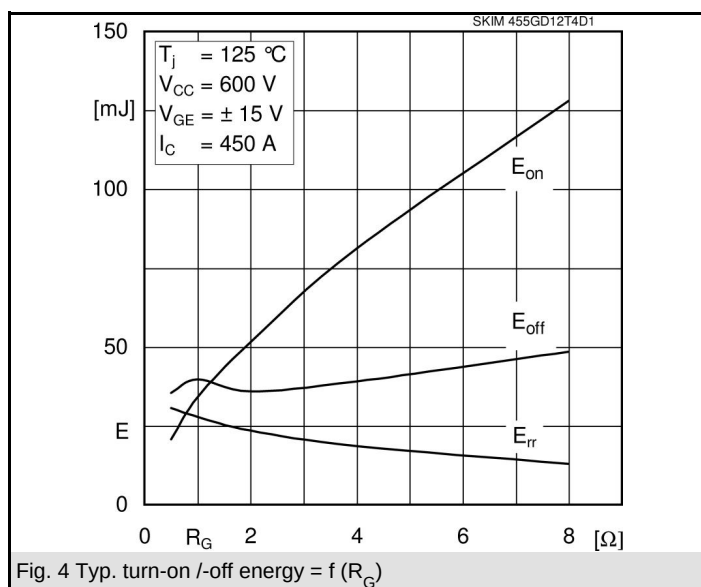
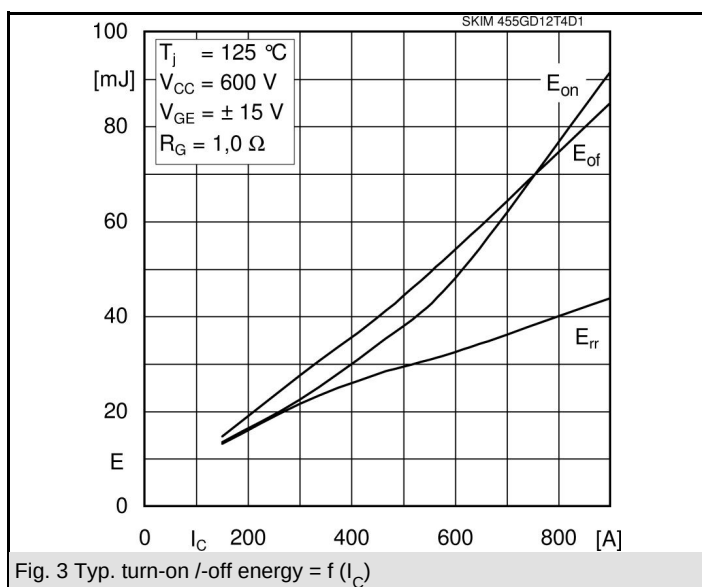
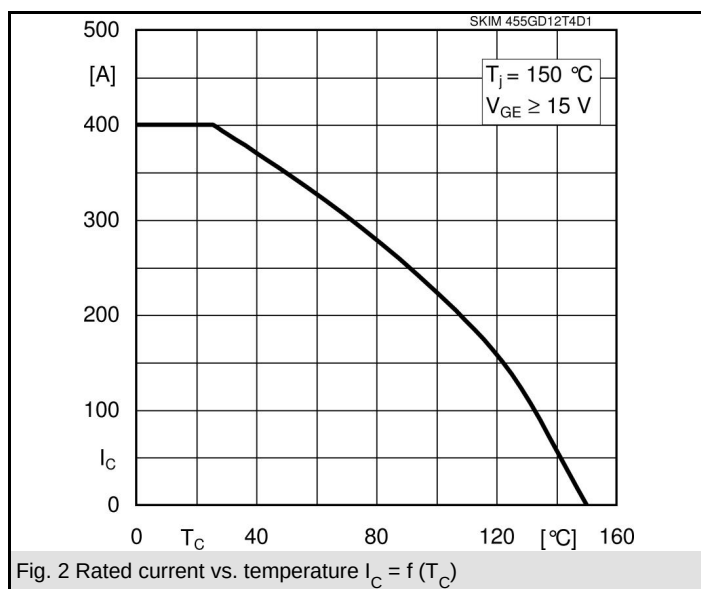
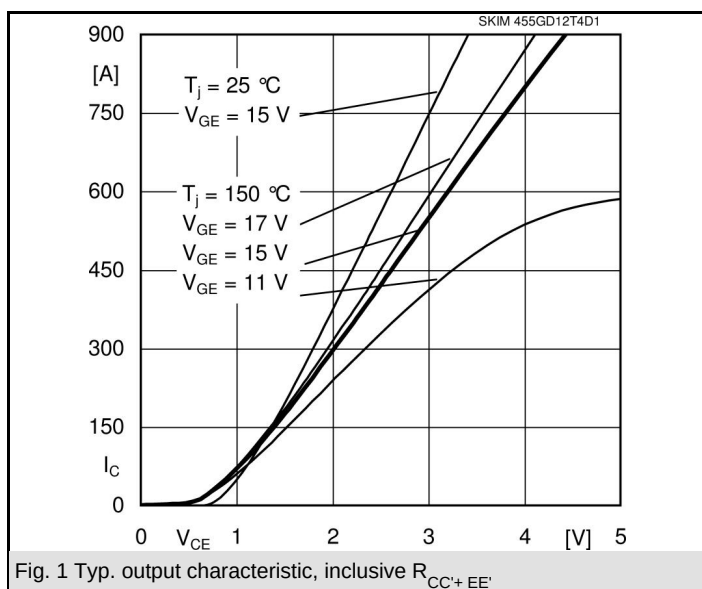
Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 450 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		2,3	2,8	V
		T _j = 125 °C _{chiplev.}		2,2	2,7	V
V _{F0}		T _j = 25 °C		1,2	1,6	V
		T _j = 125 °C		0,9	1,3	V
r _F		T _j = 25 °C		2,3	2,7	mΩ
		T _j = 125 °C		2,8	3,1	mΩ
I _{RRM}	I _F = 450 A	T _j = 125 °C		500		A
Q _{rr}	di/dt = 9000 A/μs			64,5		μC
E _{rr}	V _{GE} = -15V			27,8		mJ
R _{th(j-s)}	per diode			0,19		K/W
Module						
L _{CE}					20	nH
R _{CC'+EE'}	res., terminal-chip	T _{case} = 25 °C		0,9		mΩ
		T _{case} = 125 °C		1,1		mΩ
M _s	to heat sink M5					Nm
M _t	to terminals M6		4		5	Nm
w					460	g
Temperature sensor						
R _{TS}	T = 25 (100)°C			1 (1,67)		kΩ
Tolerance	T = 25 (100)°C			3 (2)		%

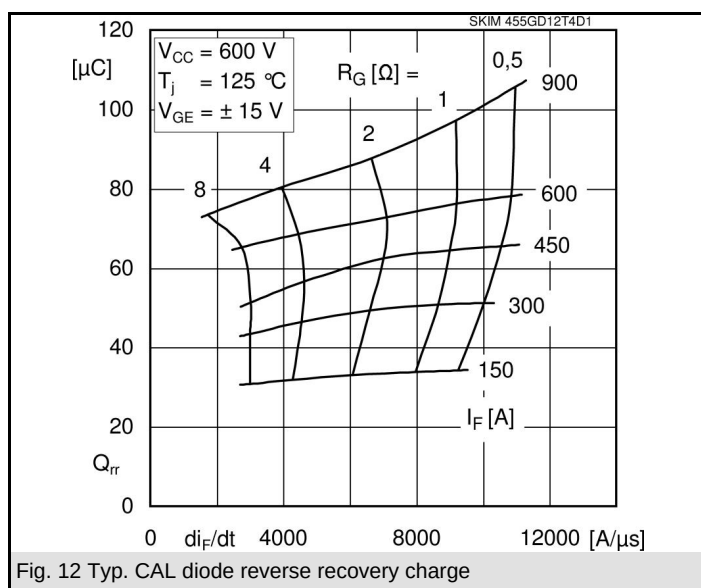
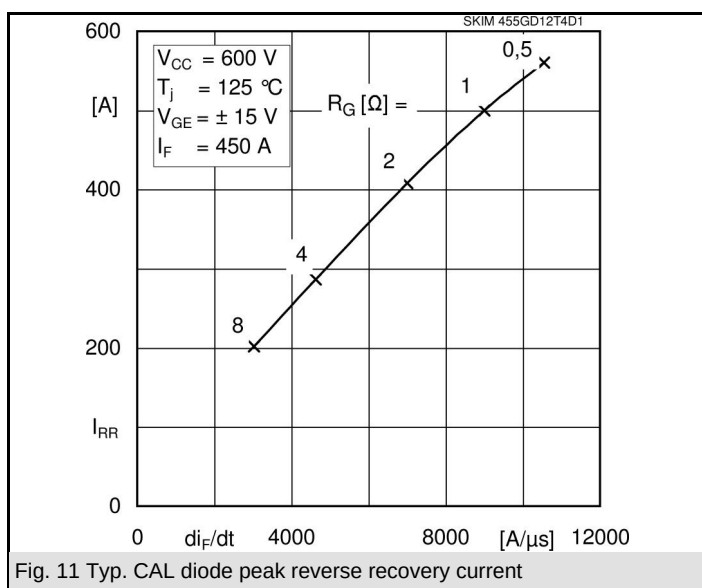
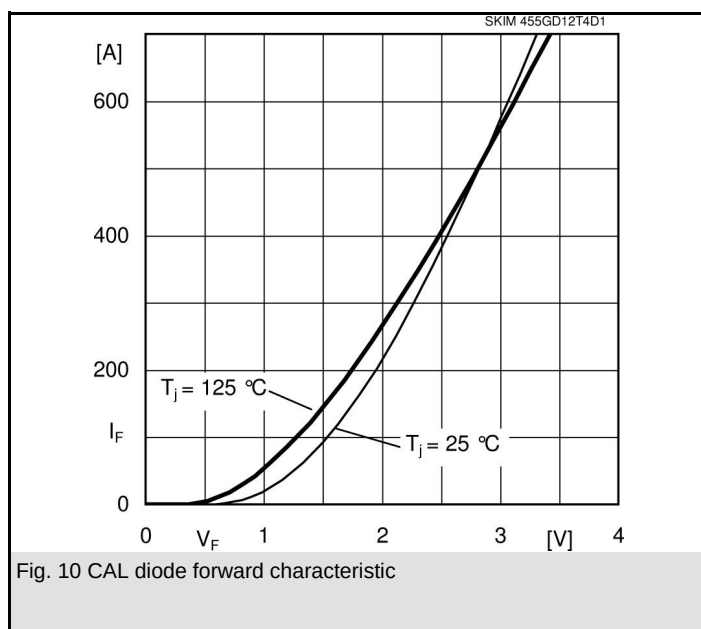
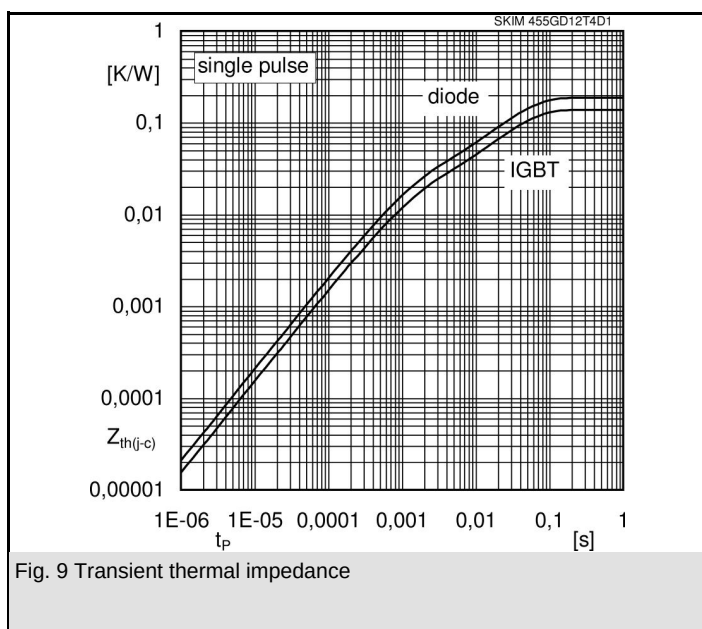
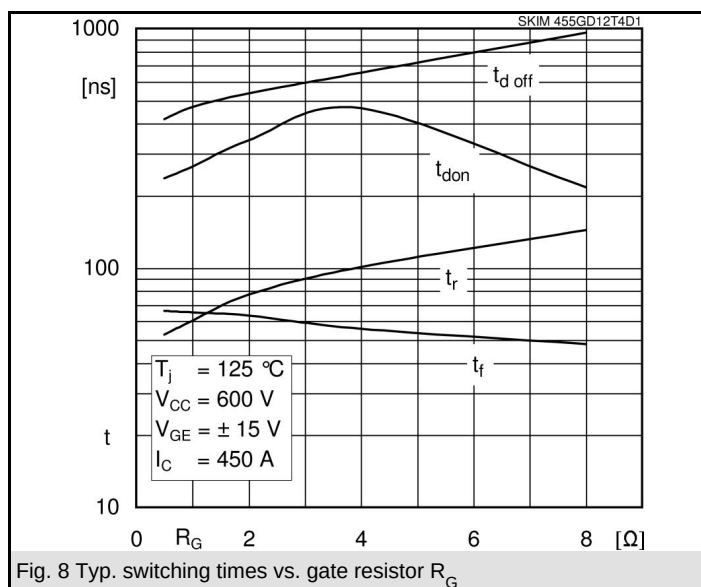
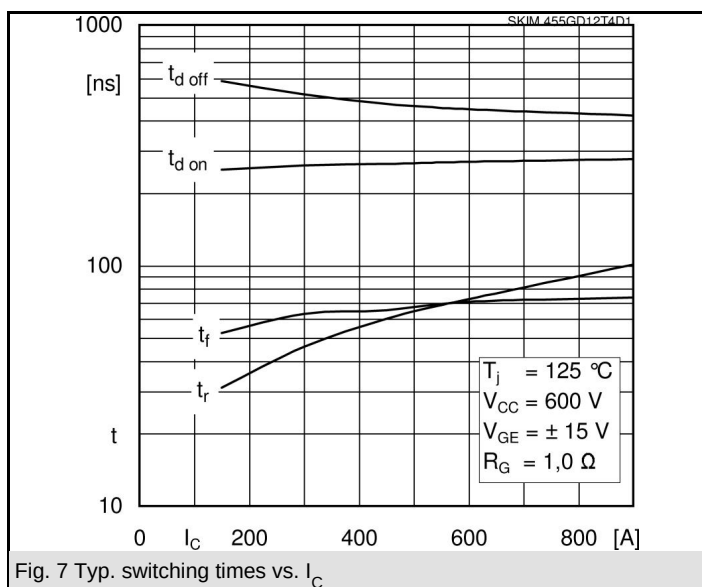
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



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UL recognized file

no. E 63 532

